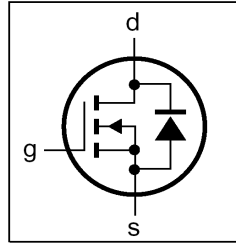


- **Ease of Paralleling**
- **Fast Switching**
- **Simple Drive Requirements**

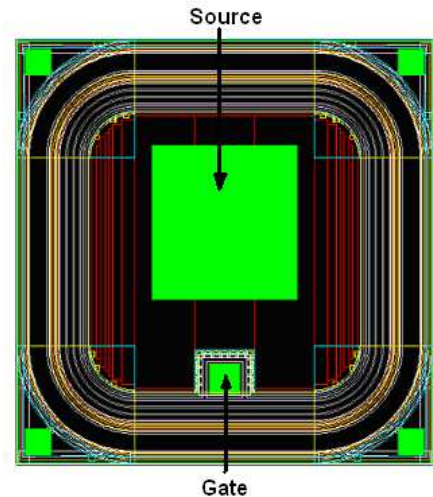


BV_{DSS}	200V
$R_{DS(ON)}$	2.0Ω
I_D	0.65A

Description

This advanced high voltage MOSFET is produced using Belling's proprietary DMOS technology. Designed for high efficiency logic level circuit.

- **Die size with scribe line** 1570 μ m X 1570 μ m
- **Scribe line** 80 μ m
- **Die Thickness** 300 \pm 20 μ m
- **Metallization**
 - **Top** Al
 - **Bottom** Ti / Ni / Ag
- **Bonding Pad Size**
 - **Gate** 140 μ m X 102 μ m
 - **Source** 540 μ m X 540 μ m
- **Passivation**



Electrical Characteristics ($T_C=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	200	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=0.65A$	-	-	2.0	Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=400\mu A$	0.5	-	1.8	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=200V, V_{GS}=0V$	-	-	0.1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}= 20V$	-	-	10	nA
V_{SD}	Forward On Voltage	$V_{GS}=0V, I_S=0.65A$	-	-	1.2	V